

SCP1060S

10A, 600V SiC Schottky Barrier Diode

Features

- Typical Forward Voltage: $V_F=1.5V$ @ $I_F=10A$
- Reverse Voltage: $V_{RRM}=600V$
- Shorter Recovery Time
- Avalanche Energy Rated

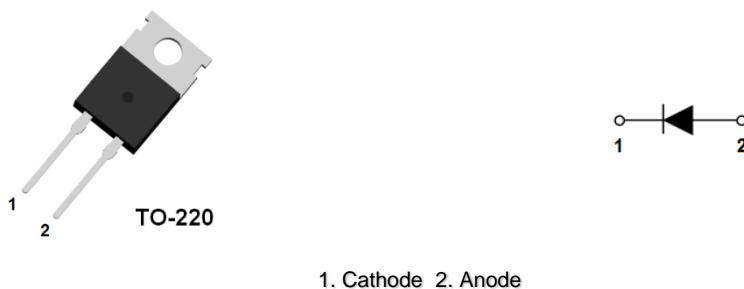
Applications

- Solar Inverter
- Uninterruptible Power Supply
- Power Factor Correction
- Switch Mode Power Supply

Description

The SCP1060S is a SiC Schottky Barrier diode with higher speed switching behavior over Si diodes. Loading of cooling system will be decreased due to the improved efficiency. This device can be used in UPS, PFC, SMPS and solar inverter.

Package Type & Internal Circuit



1. Cathode 2. Anode

Absolute Maximum Ratings

per device at $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

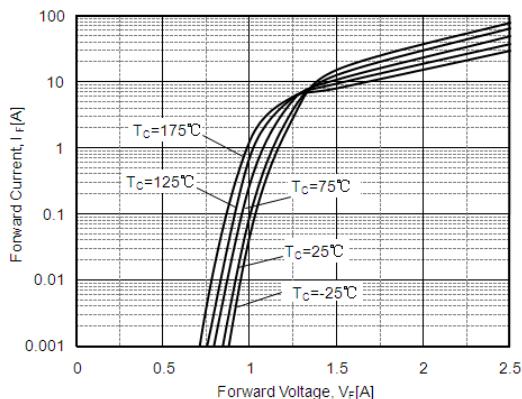
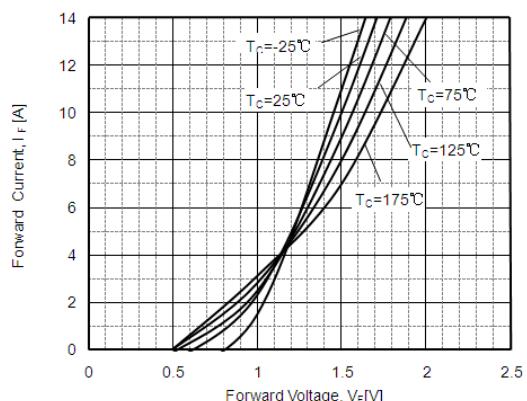
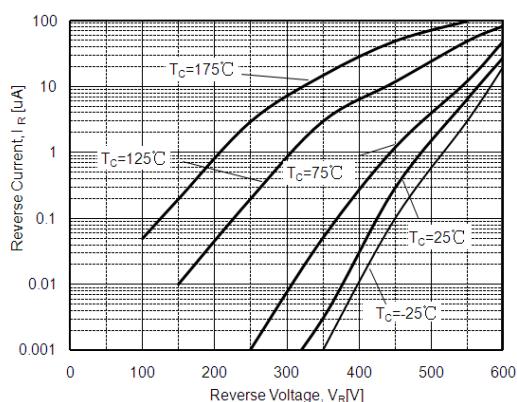
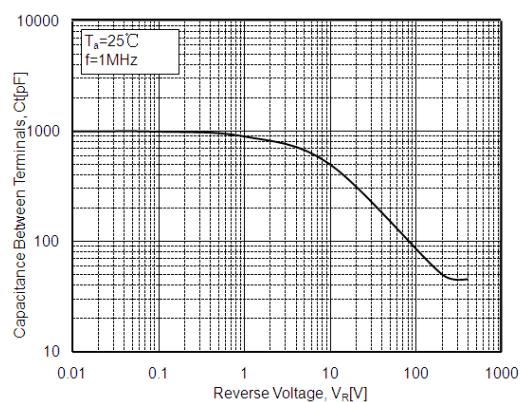
Symbol	Parameter		Ratings	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		600	V
V_{RWM}	Working Peak Reverse Voltage		600	V
V_R	DC Blocking Voltage		600	V
$I_{F(AV)}$	Average Rectified Forward Current	$T_J=150\text{ }^\circ\text{C}$	10	A
I_{FSM}	Non-repetitive Peak Surge Current	$t_p=10\text{ms}$, half sine wave	60	A
		$t_p=200\text{us}$, square wave	240	A
P_D	Power Dissipation		80	W
T_J	Operating Junction Temperature Range		-55~+175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55~+175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$	Thermal Resistance, Junction to case	1.8	$^\circ\text{C}/\text{W}$

Electrical Characteristics per device @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage Drop	$I_F=10\text{A}$	-	1.5	1.8	V
		$I_F=10\text{A}, T_J=150\text{ }^\circ\text{C}$	-	1.8	2.3	V
I_R	Reverse Leakage Current	$V_R=600\text{V}$,	-	20	-	uA
Q_c	Total Capacitive Charge	$V_R=300\text{V}, I_F=10\text{A}, di/dt=-200\text{A/us}$	-	28	-	nC
C	Total Capacitance	$V_R=0\text{V}, f=1\text{MHz}$	-	490	-	pF
		$V_R=200\text{V}, f=1\text{MHz}$	-	50	-	
		$V_R=400\text{V}, f=1\text{MHz}$	-	45	-	
t_c	Switching time	$V_R=300\text{V}, I_F=10\text{A}, di/dt=-200\text{A/us}$	-	25	-	ns

Typical Performance Characteristics
Fig. 1. Typical Characteristics: V_F vs. I_F Fig. 2. Typical Characteristics: V_F vs. I_F Fig. 3. Typical Characteristics: V_R vs. I_R Fig. 4. Typical Characteristics: V_R vs. C_t 

Package Dimensions

TO-220-2L

(Dimensions in Millimeters)

